

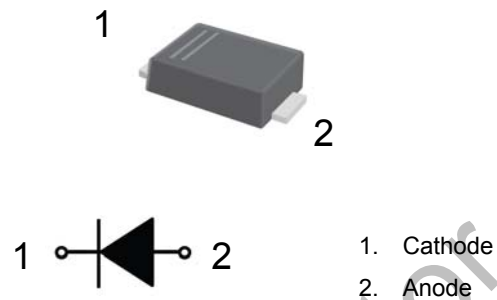


US1AF-US1MF

Features:

- ☐ For surface mounted applications
- ☐ Low profile package
- ☐ Glass Passivated Chip Junction
- ☐ High efficiency
- ☐ Easy to pick and place

SMAF



1. Cathode
2. Anode

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	US1AF	US1BF	US1DF	US1GF	US1JF	US1KF	US1MF	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _c = 125 °C	I _{F(AV)}	1							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I _{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V _F	1.0			1.3	1.65			V
Maximum DC Reverse Current T _a = 25 °C at Rated DC Blocking Voltage T _a =125 °C	I _R	5 100							μA
Maximum Reverse Recovery Time ⁽¹⁾	t _{rr}	50				75			ns
Typical Thermal Resistance ⁽²⁾	R _{θJA}	80							°C/W
Operating and Storage Temperature Range	T _j , T _{stg}	-55 ~ +150							°C

(1) Measured with $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$.

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Typical Characteristics

Fig.1 Forward Current Derating Curve

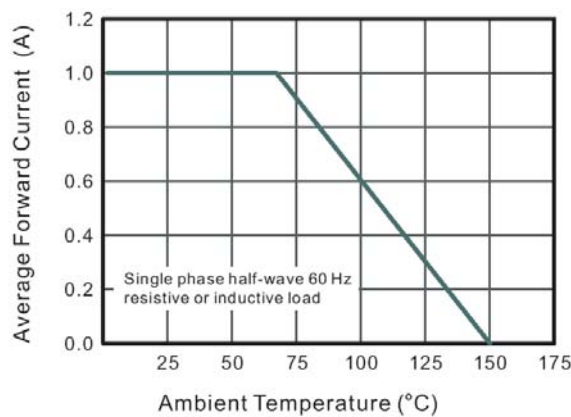


Fig.2 Typical Reverse Characteristics

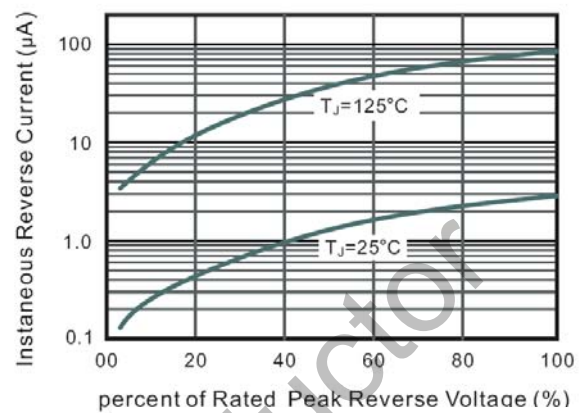


Fig.2 Forward Characteristics

Fig.3 Typical Instantaneous Forward Characteristics

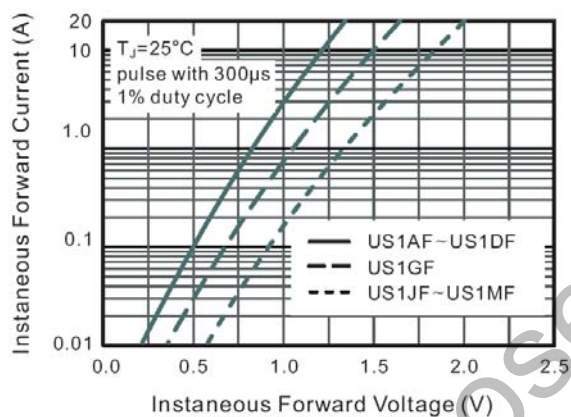
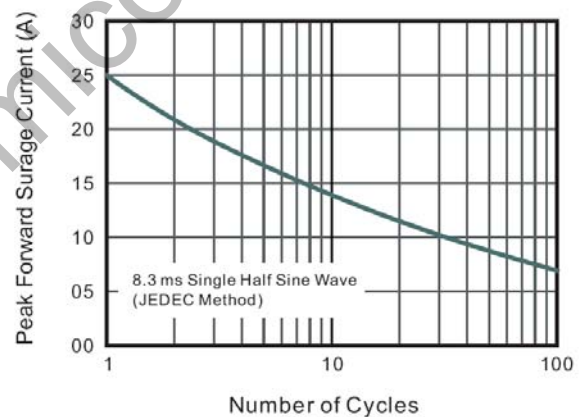
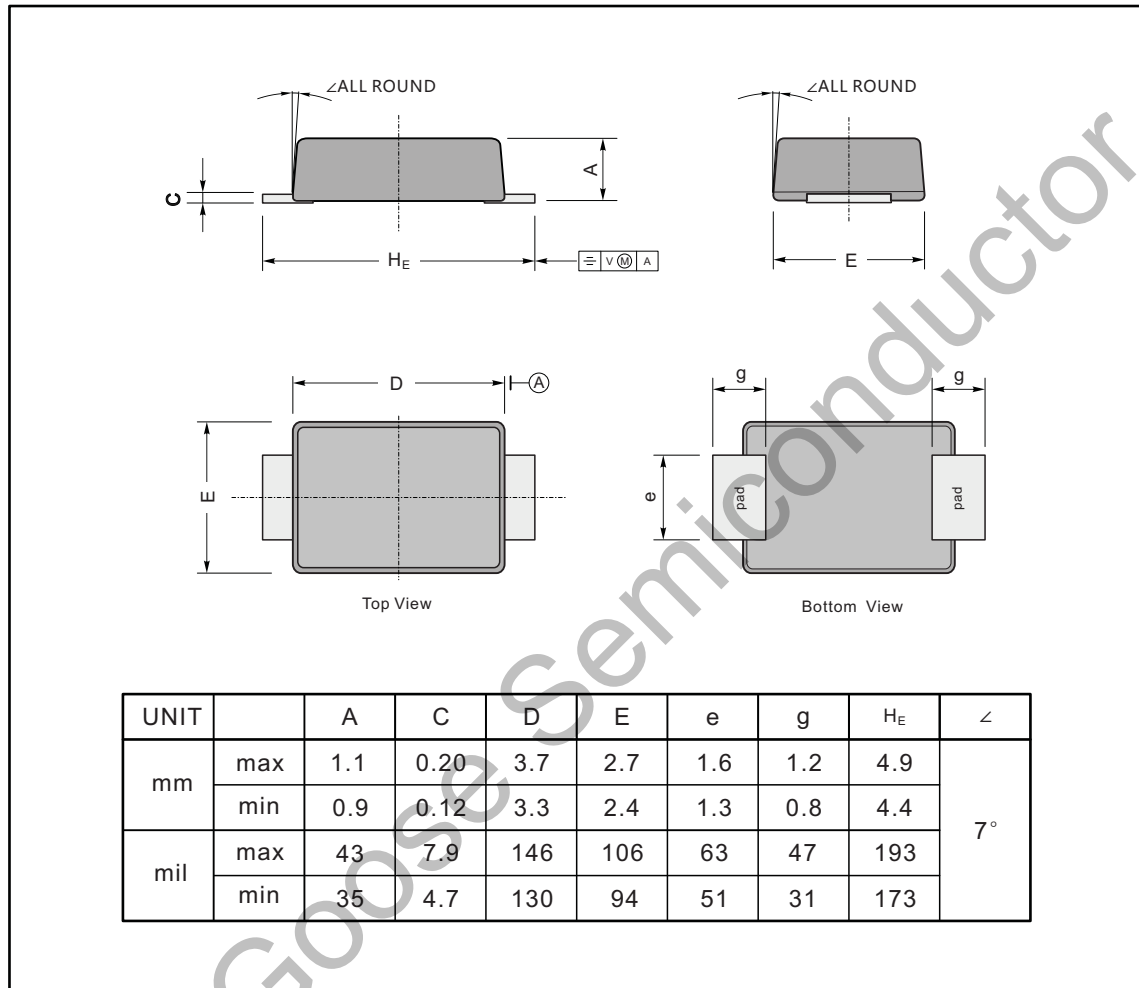
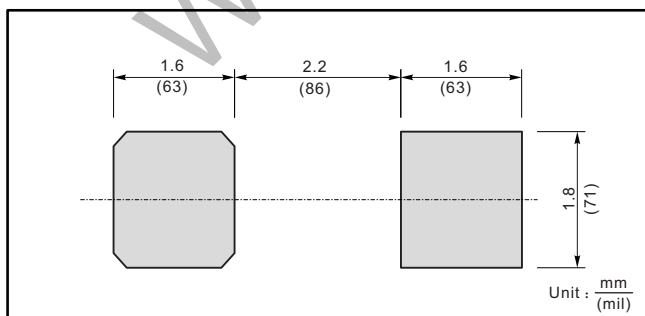


Fig.4 Maximum Non-Repetitive Peak Forward Surge Current



Package Dimension**SMAF**

Unit: mm

**The recommended mounting pad size****Marking**

Type number	Marking code
US1AF	US1A
US1BF	US1B
US1DF	US1D
US1GF	US1G
US1JF	US1J
US1KF	US1K
US1MF	US1M